AMENDMENTS TO THE CLAIMS

This listing of claims will replace all prior versions, and listings of claims in the application:

LISTING OF CLAIMS:

Claims 1-45 (Canceled)

46. (Currently Amended) A semiconductor device comprising:

a semiconductor chip having a main surface, a back surface and a plurality of side surfaces;

a plurality of electrodes arranged in a plurality of lines on the main surface of the semiconductor chip:

a base resin film formed on the main surface of the semiconductor chip and having a plurality of electrode holes formed therein, the base resin film having a first surface facing the main surface of the semiconductor chip, a second surface opposite to the first surface and a through hole provided thereof;

a plurality of conductive patterns formed on the first surface of the base resin film, the conductive patterns extending ~~near~~ in the through hole; and

an insulating film formed on the first surface of the base resin film and the conductive patterns,

wherein the conductive patterns extending in the through hole are connected with the electrodes, and a plurality of electrodes holes exposing a part of the conductive patterns.

47. (Previously presented) A semiconductor device according to claim 46, wherein the main surface and side surface of the semiconductor chip are covered by molding resin.

48. (Previously presented) A semiconductor device according to claim 46, further comprising a plurality of solder balls formed on the electrode holes.

49. (Previously presented) A semiconductor device according to claim 46, wherein the base resin film is formed on the main surface, back surface and side surfaces of the semiconductor chip.

50. (Previously presented) A semiconductor device according to claim 46, wherein the base resin film is covered by elastic resin.

51. (Previously presented) A semiconductor device according to claim 50, wherein the elastic resin is polyimide.

52. (Currently Amended) A semiconductor device comprising:

a semiconductor chip having a main surface, a back surface and a plurality of side surfaces;

a plurality of electrodes arranged in a plurality of lines on the main surface of the semiconductor chip;

a base resin film formed on the main surface of the semiconductor chip, the base resin film having a first surface facing said semiconductor chip, a second surface opposite to the first surface, a through hole and a plurality of electrode holes provided thereof;

a plurality of conductive patterns formed on the second surface of the base resin film, the conductive patterns extending ~~near~~ in the through hole;

an insulating film formed on the second surface of the base resin film and conductive patterns, wherein the conductive patterns extending in the through hole are connected with the electrodes, and a plurality of electrode holes exposing a part of the conductive patterns.

53. (Previously presented) A semiconductor device according to claim 52, wherein the main surface and side surface of the semiconductor chip are covered by molding resin.

54. (Previously presented) A semiconductor device according to claim 52, further comprising a plurality of solder balls formed on the electrodes holes.

55. (Previously presented) A semiconductor device according to claim 52, wherein the base resin film is formed on the main surface, back surface and the side surfaces of the semiconductor chip.

56. (Previously presented) A semiconductor device according to claim 52, wherein the base resin film is covered by elastic resin.

57. (Previously presented) A semiconductor device according to claim 56, wherein the elastic resin is polyimide.

58. (Previously presented) A semiconductor device comprising:

a semiconductor chip having a main surface, a back surface and a plurality of side surfaces;

a plurality of electrodes arranged in a plurality of lines on the main surface of the semiconductor chip;

a base resin film formed on the main surface of the semiconductor chip, the base resin film having a first surface facing said semiconductor chip and a second surface opposite the first surface and having a plurality of second electrode holes;

a plurality of electrode patterns formed on the first surface of the base resin film;

a first insulating film formed on the first surface of the base resin film, the first insulating film having a plurality of first electrode holes for exposing the electrode patterns;

a plurality of conductive patterns formed on the second surface of the base resin film, the conductive patterns electrically connected to the electrode patterns; and

a second insulating film formed on the second surface of the base resin film and the conductive patterns, wherein the second electrode holes expose a part of the conductive patterns.

59. (Previously presented) A semiconductor device according to claim 58, wherein the main surface and the side surface of the semiconductor chip are covered by molding resin.

60. (Previously presented) A semiconductor device according to claim 58, further comprising a plurality of solder balls formed on the second electrodes holes.

61. (Previously presented) A semiconductor device according to claim 58, wherein the base resin film is formed on the main surface, back surface and the side surfaces of the semiconductor chip.

62. (Previously presented) A semiconductor device according to claim 61, wherein the base resin film is substantially surrounding the semiconductor chip.

63. (Previously presented) A semiconductor device according to claim 58, wherein the base resin is covered by elastic resin.

64. (Previously presented) A semiconductor device according to claim 63, wherein the elastic resin is polyimide.